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SEMICONDUCTOR



ESD



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PLED

MS8205A

Product specification

Description

The MS8205A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

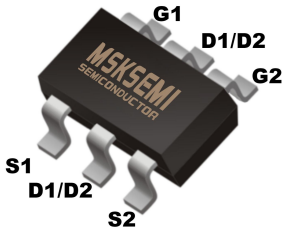
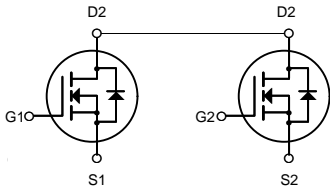

General Features

- $V_{DS}=20V, I_D = 6A$
- $R_{DS(ON)} < 25m\Omega @ V_{GS}=4.5V$

Application

- Battery protection
- Load switch
- Power management

Reference News

PACKAGE OUTLINE	Dual N-Channel MOSFET	Marking
 <p>SOT-23-6L</p>		

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 10	V
$I_D @ T_A=25^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	6	A
I_{DM}	Pulsed Drain Current ¹	25	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	100	$^\circ C/W$

Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	21	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 19.5V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4A	-	22	25	mΩ
		V _{GS} =2.5V, I _D =3A	-	26	31	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =4A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =8V,V _{GS} =0 V, F=1.0MHz	-	600	-	PF
Output Capacitance	C _{oss}		-	330	-	PF
Reverse Transfer Capacitance	C _{rss}		-	140	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,I _D =1A V _{GS} =4V,R _{GEN} =10 Ω	-	18	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	43	-	nS
Turn-Off Fall Time	t _f		-	20	-	nS
Total Gate Charge	Q _g	V _{DS} =10V,I _D =4 A, V _{GS} =4.5V	-	11	-	nC
Gate-Source Charge	Q _{gs}		-	2.3	-	nC
Gate-Drain Charge	Q _{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2A	-	0.8	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	2	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

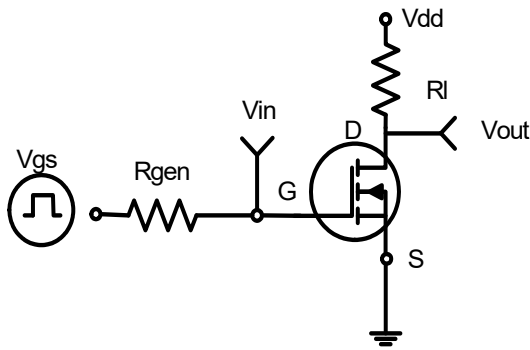


Figure 1: Switching Test Circuit

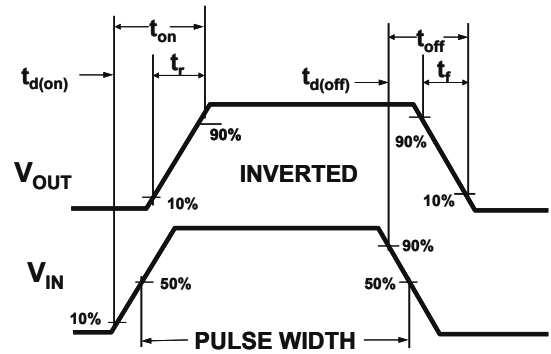


Figure 2: Switching Waveforms

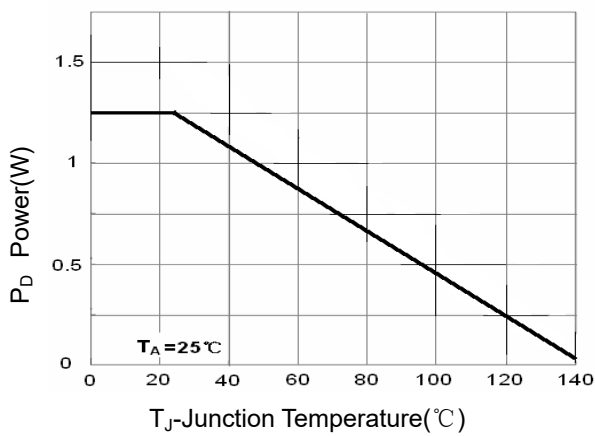


Figure 3 Power Dissipation

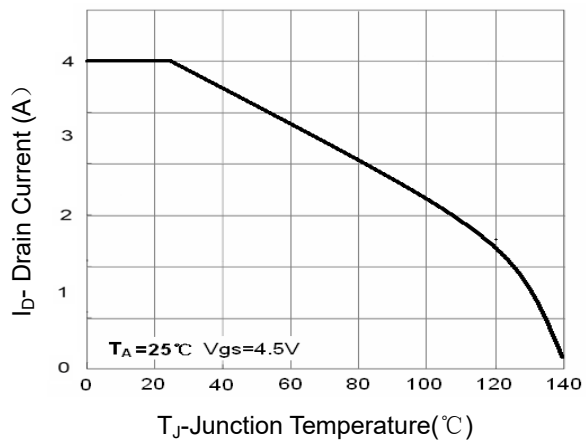


Figure 4 Drain Current

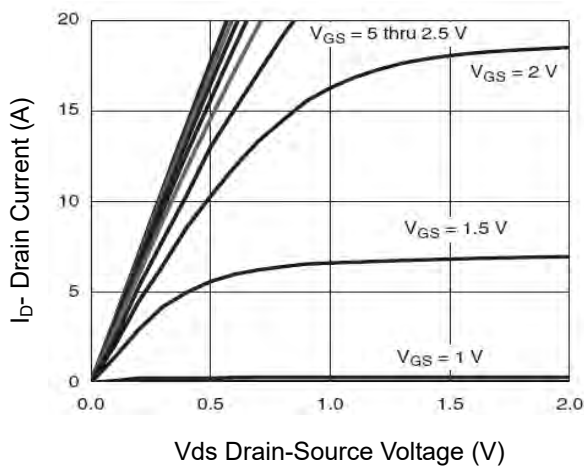


Figure 5 Output Characteristics

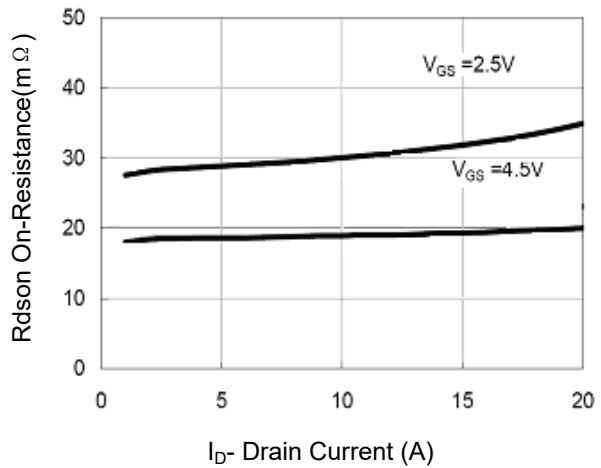


Figure 6 Drain-Source On-Resistance

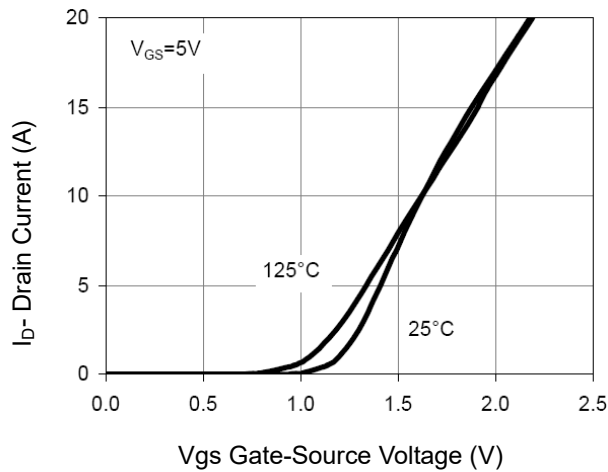


Figure 7 Transfer Characteristics

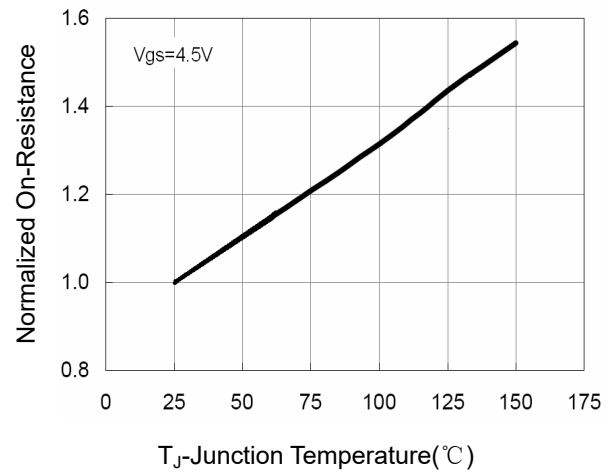


Figure 8 Drain-Source On-Resistance

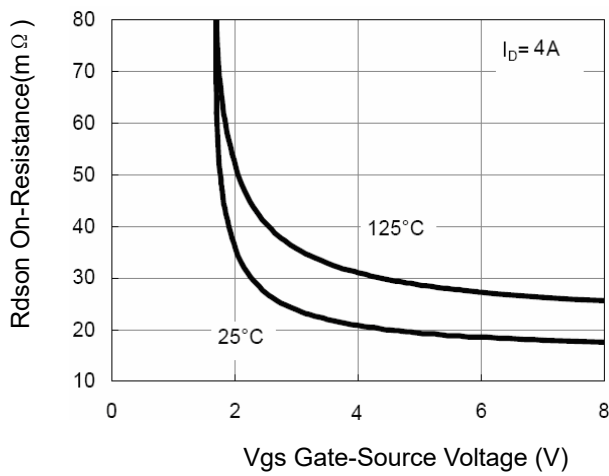


Figure 9 Rdson vs Vgs

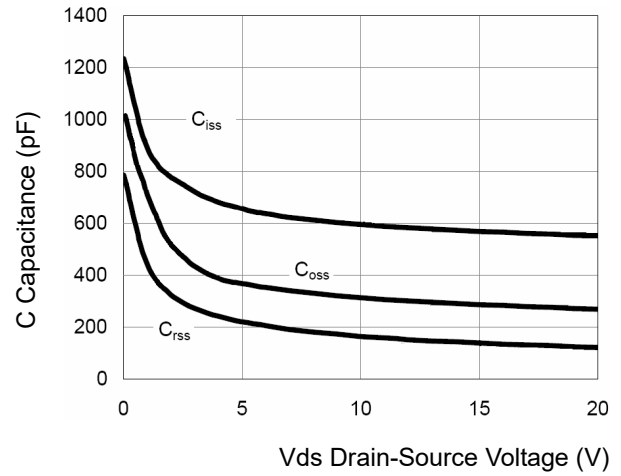


Figure 10 Capacitance vs Vds

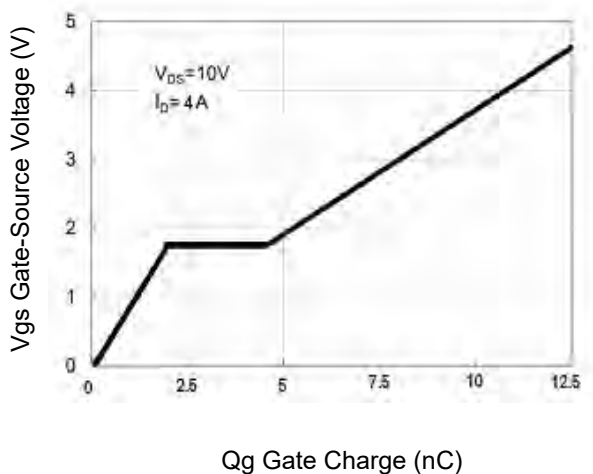


Figure 11 Gate Charge

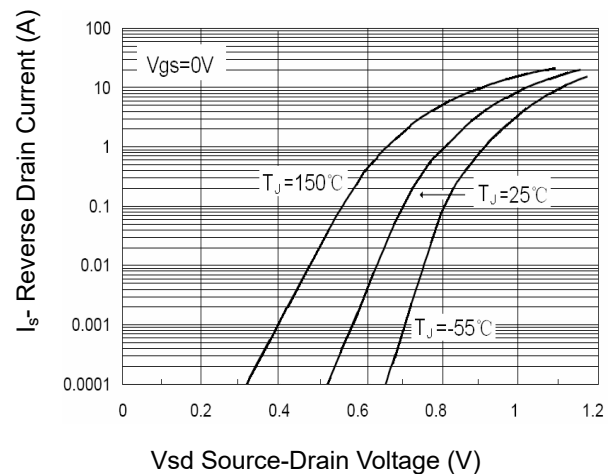


Figure 12 Source- Drain Diode Forward

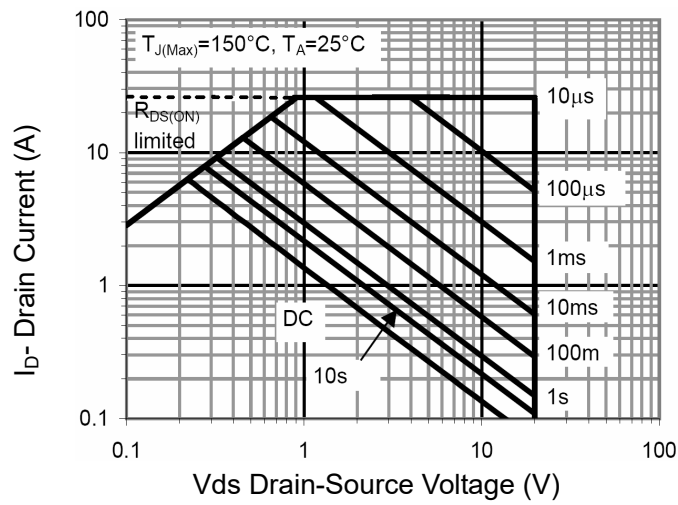


Figure 13 Safe Operation Area

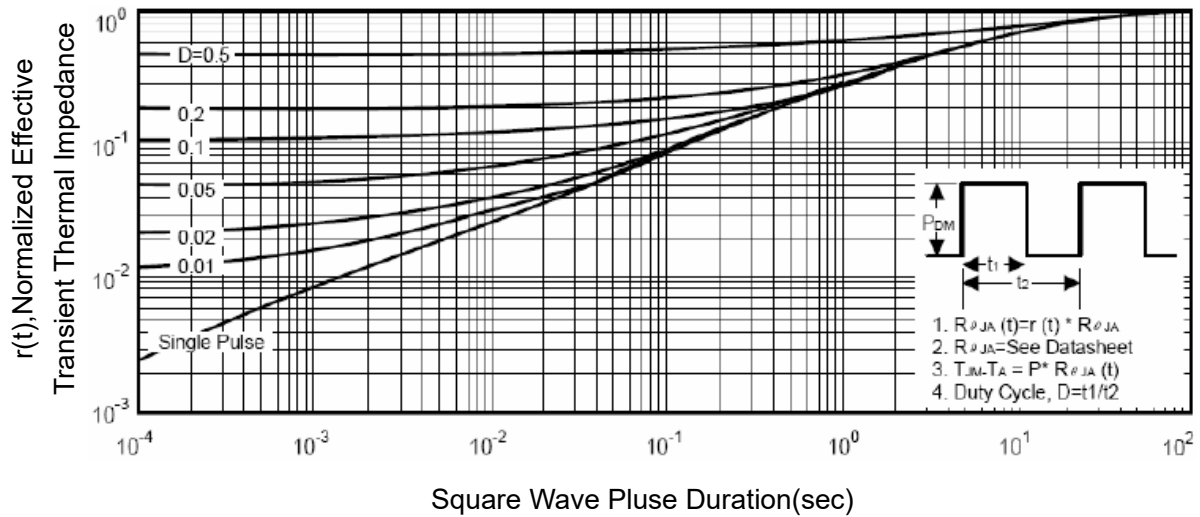
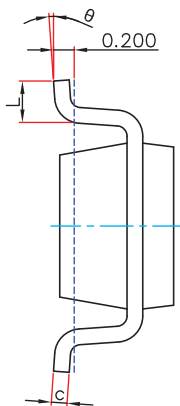
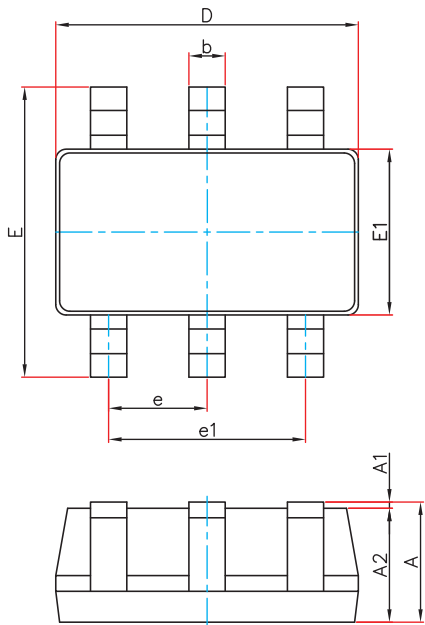


Figure 14 Normalized Maximum Transient Thermal Impedance

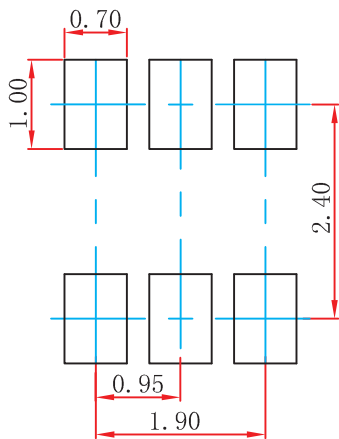
SOT-23-6L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

M 2012 P A

SOT-23-6L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MS8205A	SOT-23-6L	3000

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